Octal Transparent Latches (with 3-state outputs)

HITACHI

Description

When the latch enable (LE) input is high, the Q outputs of HD74HCT563 will follow the inversion of the D inputs and the Q outputs of HD74HCT573 will follow the D inputs.

When the latch enable goes low, data at the D inputs will be retained at the outputs until latch enabled returns high again. When a high logic level is applied to the output control input, all outputs go to a high impedance state, regardless of what signals are present at the other inputs and the state of the storage elements.

Features

- LSTTL Output Logic Level Compatibility as well as CMOS Output Compatibility
- High Speed Operation: t_{pd} (D to Q, \overline{Q}) = 13 ns typ ($C_L = 50 \text{ pF}$)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 4.5$ to 5.5 V
- Low Input Current: 1 μA max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max (Ta = 25°C)

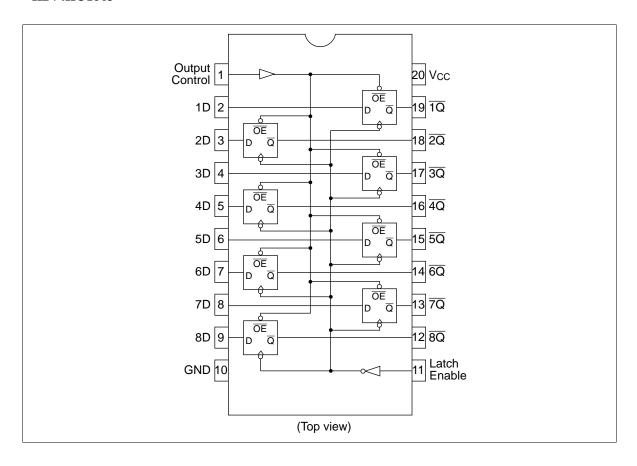
Function Table

			Outputs	
Output Control	Latch Enable	Data	HD74HCT563	HD74HCT573
L	Н	Н	L	Н
L	Н	L	Н	L
L	L	Х	$\overline{Q}_{\scriptscriptstyle{0}}$	Q_0
Н	Х	Х	Z	Z

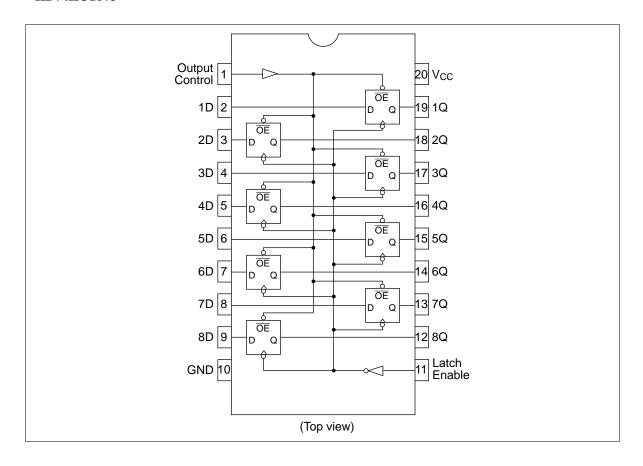


Pin Arrangement

HD74HCT563

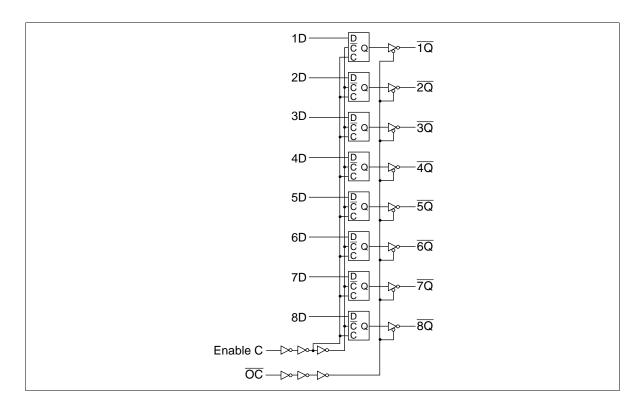


HD74HCT573

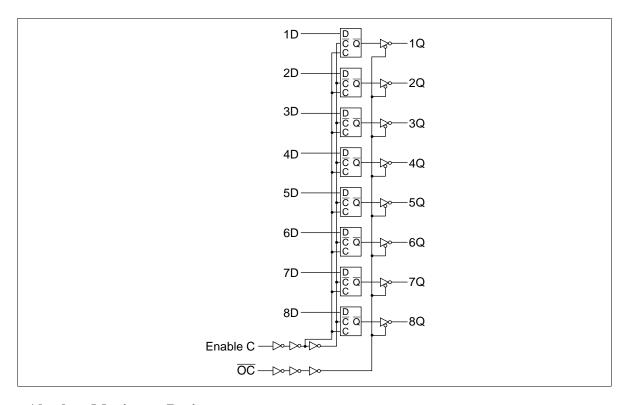


Block Diagram

HD74HCT563



HD74HCT573



Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V _{cc}	-0.5 to +7.0	V
Input voltage	V_{IN}	-0.5 to V_{cc} + 0.5	V
Output voltage	V_{OUT}	-0.5 to V_{cc} + 0.5	V
DC current drain per pin	I _{OUT}	±35	mA
DC current drain per V _{cc} , GND	$I_{\rm CC},I_{\rm GND}$	±75	mA
DC input diode current	I _{IK}	±20	mA
DC output diode current	I _{ok}	±20	mA
Power dissipation per package	P _T	500	mW
Storage temperature	Tstg	-65 to +150	°C

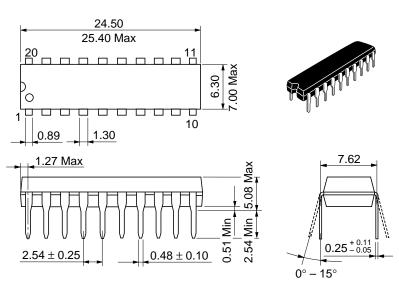
DC Characteristics

		Ta =	: 25°C	;	Ta = - +85°0	–40 to		Test Co	onditions
Item	Symbol	Min	Тур	Max	Min	Max	Unit	V _{cc} (V)	-
Input voltage	V_{IH}	2.0	_	_	2.0	_	V	4.5 to 5.5	
	V _{IL}	_	_	8.0	_	8.0	V	4.5 to 5.5	
Output voltage	V _{OH}	4.4	_	_	4.4	_	V	4.5	Vin = V_{IH} or V_{IL} I_{OH} = $-20 \mu A$
		4.18	_	_	4.13	_	_	4.5	$I_{OH} = -6 \text{ mA}$
	V_{OL}	_	_	0.1	_	0.1	V	4.5	Vin = V_{IH} or V_{IL} I_{OL} = 20 μ A
		_	_	0.26	_	0.33		4.5	$I_{OL} = 6 \text{ mA}$
Off-state output current	I _{oz}	_	_	±0.5	_	±5.0	μΑ	5.5	$Vin = V_{IH} \text{ or } V_{IL},$ $Vout = V_{CC} \text{ or GND}$
Input current	lin	_	_	±0.1	_	±1.0	μΑ	5.5	Vin = V _{CC} or GND
Quiescent current	I _{cc}	_	_	4.0	_	40	μΑ	5.5	Vin = V_{CC} or GND, lout = 0 μ A

AC Characteristics ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

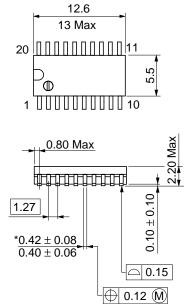
		Ta =	25°C	;	Ta = - +85°0	-40 to		Test Co	onditions
Item	Symbol	Min	Тур	Max	Min	Max	Unit	V _{cc} (V)	-
Propagation delay	t _{PLH}	_	13	22	_	28	ns	4.5	Data to Q, Q
time	$t_{\tiny PHL}$	_	13	22	_	28		4.5	
	t _{PLH}	_	14	23	_	29	ns	4.5	Enable G to Q, Q
	t _{PHL}	_	14	23	_	29		4.5	_
Output enable	t_{zL}	_	14	30	_	38	ns	4.5	
time	t _{zH}	_	15	30	_	38	_	4.5	-
Output disable	t _{LZ}	_	16	30	_	38	ns	4.5	
time	t _{HZ}	_	17	30	_	38	_	4.5	-
Setup time	t _{su}	12	3	_	15	_	ns	4.5	
Hold time	t _h	5	-1	_	5	_	ns	4.5	
Pulse width	t _w	16	4	_	20	_	ns	4.5	
Output rise/fall	t _{TLH}	_	4	12	_	15	ns	4.5	
time	t _{THL}	_	4	12	_	15		4.5	-
Input capacitance	Cin	_	5	10	_	10	pF	_	

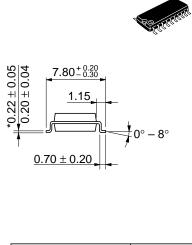
Unit: mm



Hitachi Code	DP-20N
JEDEC	_
EIAJ	Conforms
Weight (reference value)	1.26 g

Unit: mm





Hitachi Code	FP-20DA
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.31 a

*Dimension including the plating thickness
Base material dimension

 $10.40^{+0.25}_{-0.40}$ $^*0.27 \pm 0.05$ 1.45 $0.70^{+0.57}_{-0.30}$ Hitachi Code JEDEC FP-20DB

Weight (reference value) 0.52 g

EIAJ

Conforms

Unit: mm

*Dimension including the plating thickness
Base material dimension

 $^{*}0.42 \pm 0.08$ 0.40 ± 0.06

1.27

12.8 13.2 Max 20 1 11

1 10 10 10 10

0.935 Max

Φ

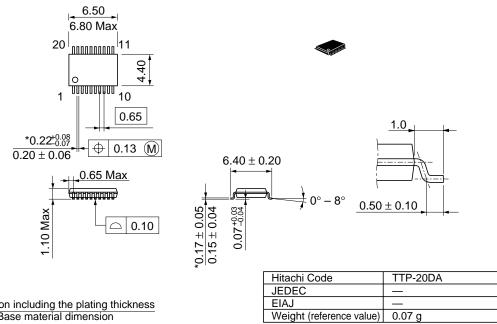
7.50

0.15

0.12 M

2.65 Max

Unit: mm



*Dimension including the plating thickness
Base material dimension

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